



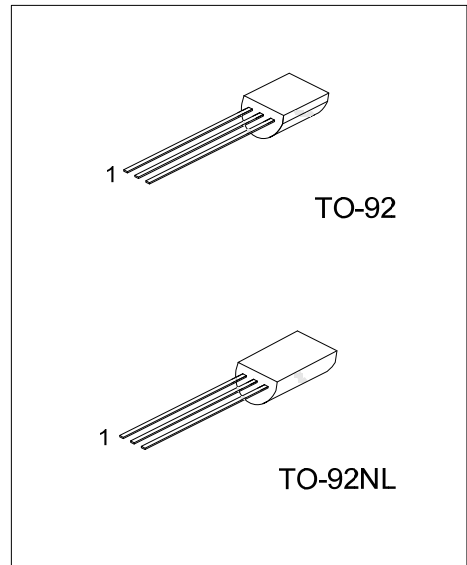
2SD1857

NPN EPITAXIAL SILICON TRANSISTOR

POWER TRANSISTOR

FEATURES

- * High breakdown voltage. ($BV_{CEO}=120V$)
- * Low collector output capacitance. (Typ. 20pF at $V_{CB}=10V$)
- * High transition frequency. ($f_T=80MHz$)



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SD1875L-x-T92-B	2SD1875G-x-T92-B	TO-92	E	C	B	Tape Box
2SD1875L-x-T92-K	2SD1875G-x-T92-K	TO-92	E	C	B	Bulk
2SD1875L-x-T92-R	2SD1875G-x-T92-R	TO-92	E	C	B	Tape Reel
2SD1875L-x-T9N-B	2SD1875G-x-T9N-B	TO-92NL	E	C	B	Tape Box
2SD1875L-x-T9N-K	2SD1875G-x-T9N-K	TO-92NL	E	C	B	Bulk

Note: Pin Assignment E: EMITTER C: COLLECTOR B: BASE

2SD1857L-x-T92-B (1) Packing Type (2) Package Type (3) Rank (4) Lead Free		(1) B: Tape Box, K: Bulk, T: Tape Reel (2) T92: TO-92, T9N: TO-92NL (3) x: refer to Classification of h_{FE} (4) G: Halogen Free, L: Lead Free
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■ ABSOLUTE MAXIMUM RATING ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	120	V
Emitter-base voltage	V_{EBO}	5	V
Collector power dissipation	P_C	1	W
Collector current	I_C	2	A
Collector current	I_{CP}	3	A
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-40 ~ +150	$^\circ\text{C}$

Note 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV_{CBO}	$I_C=50\mu\text{A}$	120			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C=1\text{mA}$	120			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E=50\mu\text{A}$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=100\text{V}$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}$			1	μA
DC current transfer ratio	h_{FE}	$V_{CE}=5\text{V}$, $I_C=0.1\text{A}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=I_B=1\text{A}/0.1\text{A}$ (Note)			0.4	V
Transition frequency	f_T	$V_{CE}=5\text{V}$, $I_E=-0.1\text{A}$, $f=30\text{MHz}$		80		MHz
Output capacitance	C_{ob}	$V_{CB}=10\text{V}$, $I_E=0\text{A}$, $f=1\text{MHz}$ (Note)		20		pF

Note: Measured using pulse current.

■ CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82-180	120-270	180-390

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